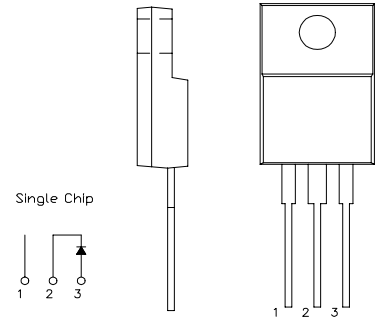


SBD Type : FSH10A04B

OUTLINE DRAWING

FEATURES

- *Similar to TO-220AB Case
- *Fully Molded Isolation
- *Low Forward Voltage Drop
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *Tj=150 °C operation



Maximum Ratings

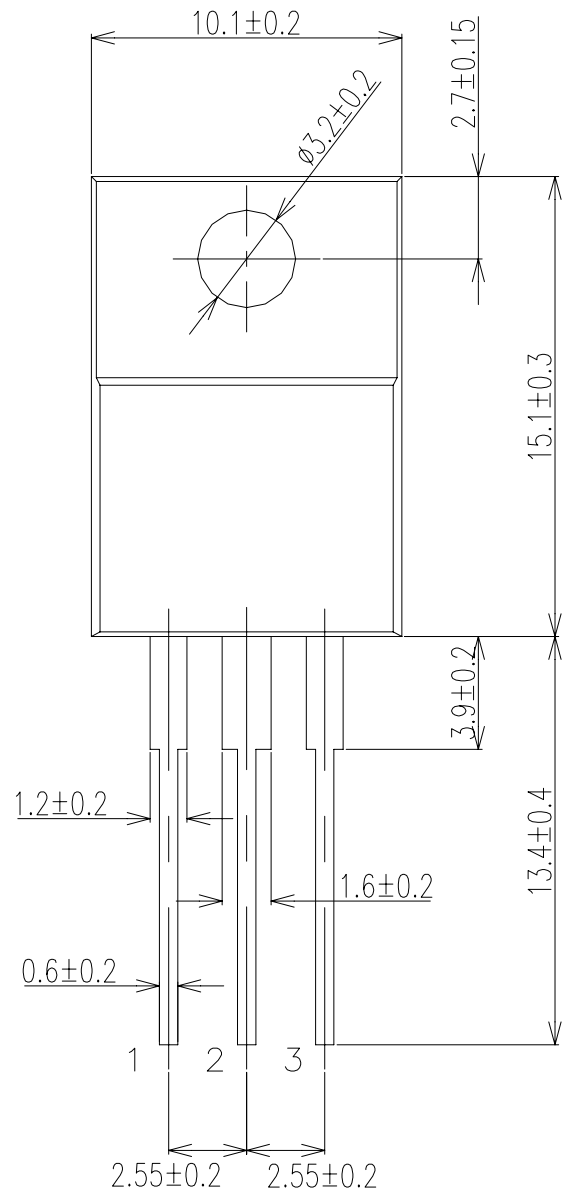
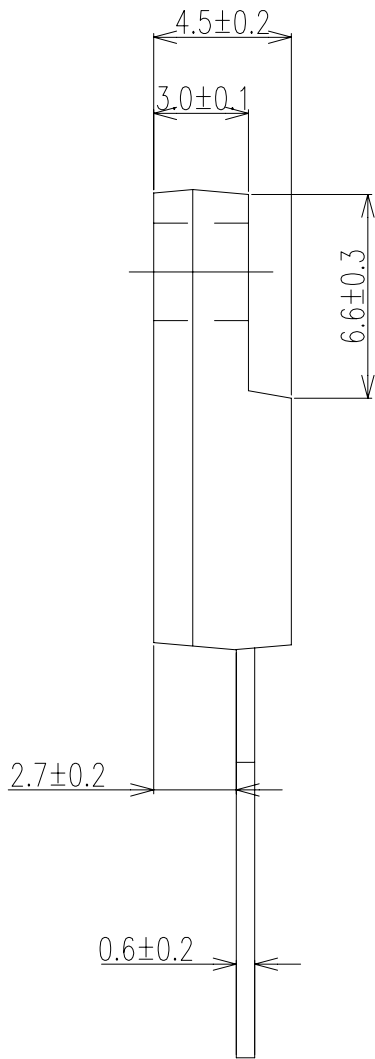
Approx Net Weight: 1.75g

Rating	Symbol	FSH10A04B		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40		V
Repetitive Peak Surge Reverse Voltage	V_{RRSM}	45(pulse width $\leq 1\mu s$ duty $\leq 1/50$)		V
Average Rectified Output Current	I_O	10	$T_c=127^\circ C$ 50 Hz half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	I_{FSM}	180	50Hz Half Sine Wave ,1cycle Non-repetitive	A
Operating JunctionTemperature Range	T_{jw}	-40 to +150		$^\circ C$
Storage Temperature Range	T_{stg}	-40 to +150		$^\circ C$
Mounting torque	F_{tor}	recommended torque = 0.5		N·m

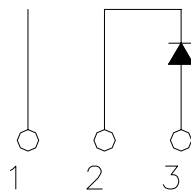
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j= 25^\circ C, V_{RM}= V_{RRM}$	-	-	1	mA
Peak Forward Voltage	V_{FM}	$T_j= 25^\circ C, I_{FM}= 10 A$	-	-	0.61	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	3	$^\circ C /W$
	$R_{th(c-f)}$	Cace to Fin	-	-	1.5	$^\circ C /W$

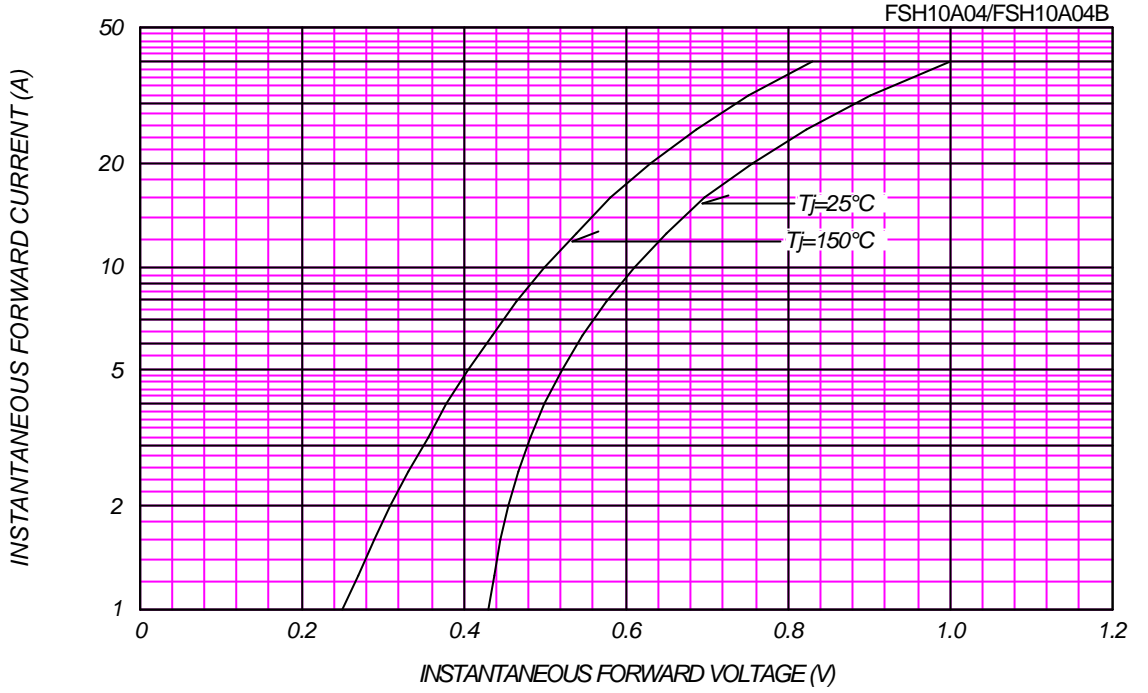
FSH_A_B OUTLINE DRAWING (Dimensions in mm)



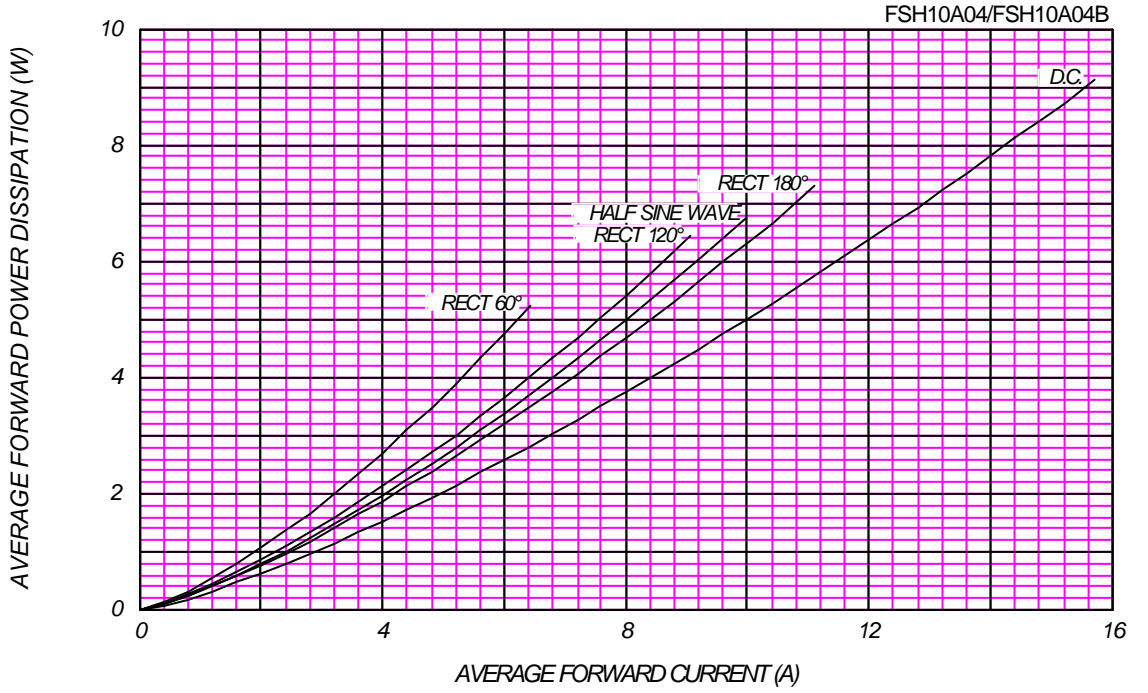
Single Chip



FORWARD CURRENT VS. VOLTAGE



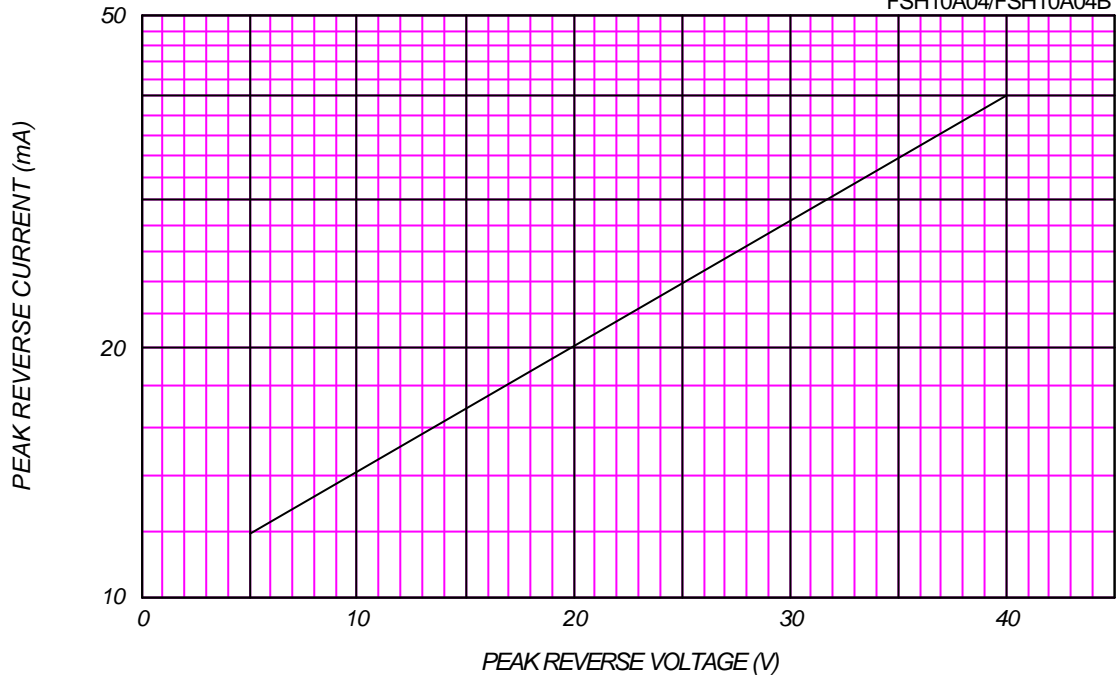
AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

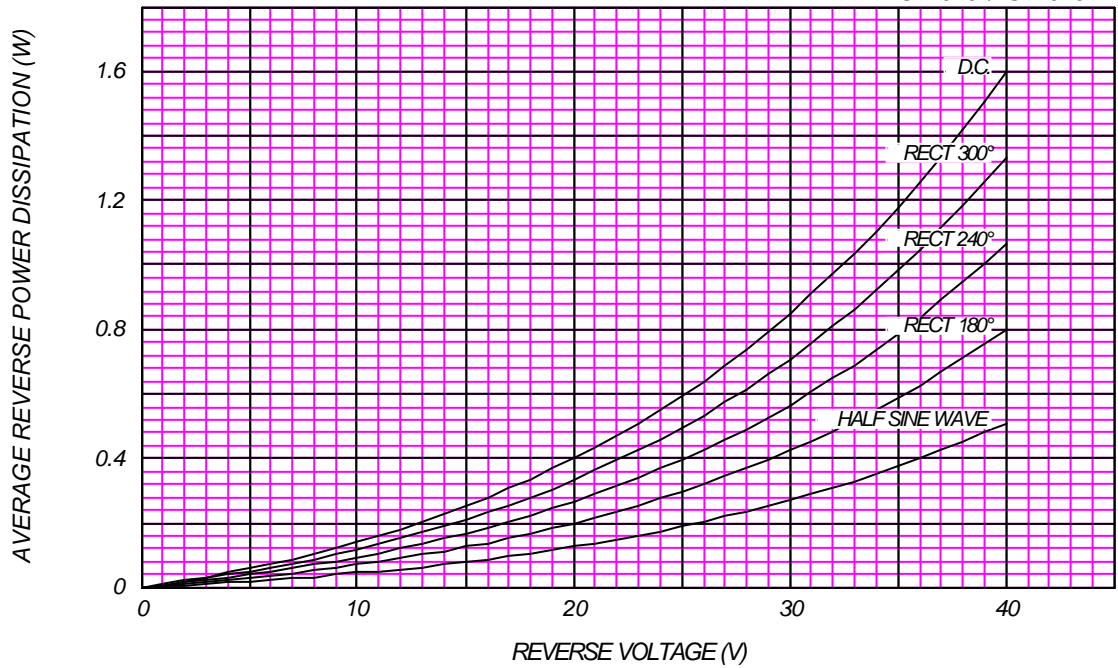
$T_j = 150\text{ }^\circ\text{C}$

FSH10A04/FSH10A04B



AVERAGE REVERSE POWER DISSIPATION

FSH10A04/FSH10A04B

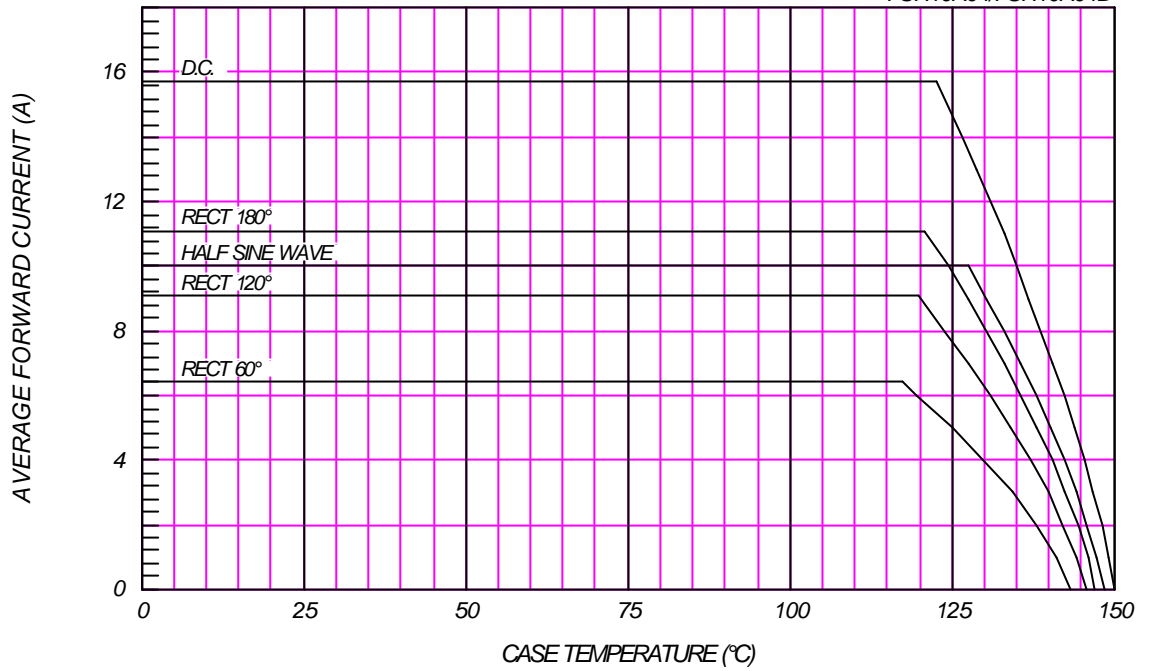




AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM}=40V$

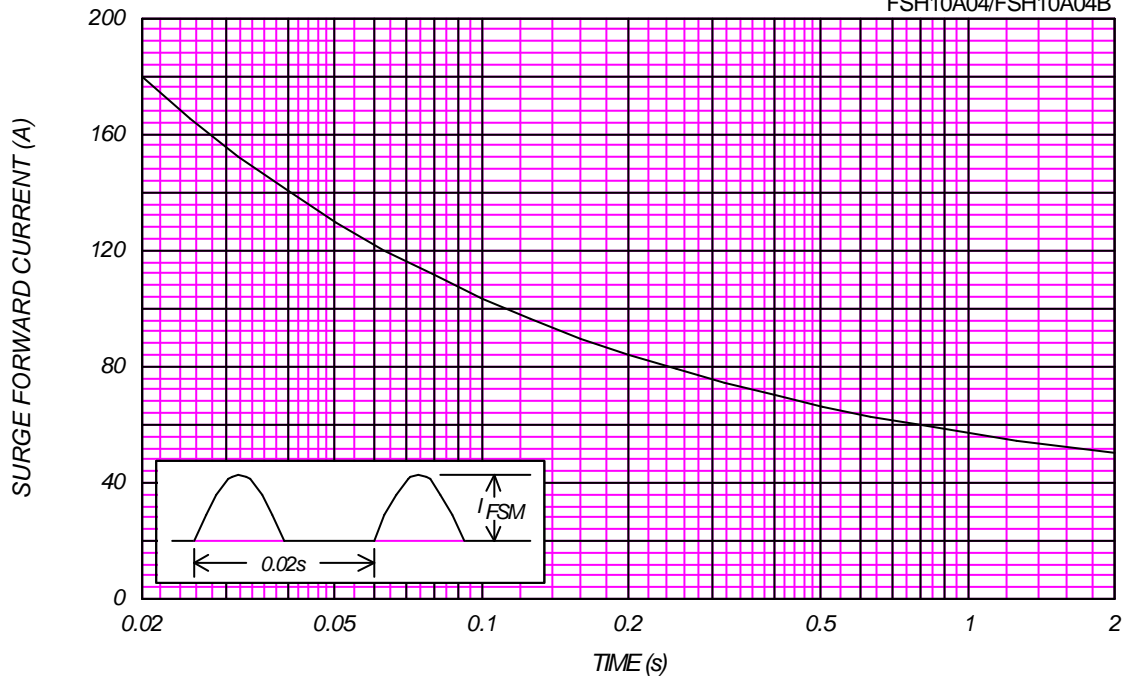
FSH10A04/FSH10A04B



SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

FSH10A04/FSH10A04B



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^\circ\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

FSH10A04/FSH10A04B

